

In the Claims:

Claim 8 (amended). The method according to claim 7, which further comprises choosing the magnitude of the doping of the further buffer layer such that, in an operating state in which
5 the semiconductor component effects blocking in the direction from the drain contact toward the source contact, at least in an envisaged range of applied electrical voltages, a space charge zone present in the first base region is formed in a manner extending at least as far as the further buffer layer.

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